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10ES32

**Third Semester B.E. Degree Examination, Dec.2019/Jan.2020**  
**Analog Electronic Circuits**

Max. Marks:100

Note: Answer FIVE full questions, selecting atleast TWO questions from each part.

**PART - A**

- 1 a. Explain the following with respect to a semi conductor diode.  
 i) Transition capacitance ii) Reverse necessary time iii) Piece-wise linear model. (06 Marks)
- b. For the circuit shown in Fig.Q1(b) Find and plot the waveforms of 'V<sub>o</sub>' for the input indicated. (06 Marks)

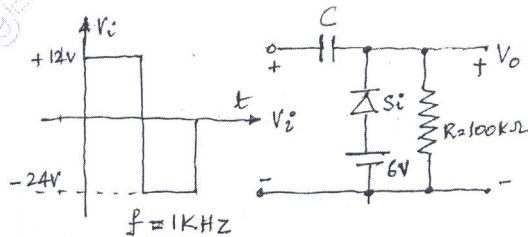


Fig.Q1(b)

- c. For the circuit shown in Fig.Q1(c) :  
 i) Explain the operation of the circuit  
 ii) Calculate DC o/p voltage and current  
 iii) Find average and peak diode currents.  
 iv) Calculate the required PIV rating of each diode.  
 Assume ideal diodes and take R<sub>1</sub> = R<sub>2</sub> = R = 10kΩ. (08 Marks)

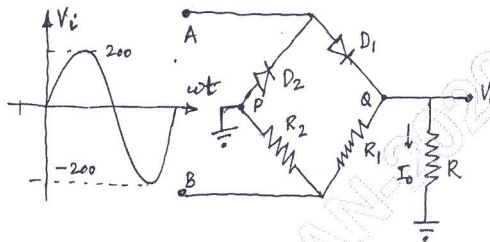


Fig.Q1(c)

- 2 a. Derive an expression for stability factor S(I<sub>CO</sub>) and S(V<sub>BE</sub>) for collector feedback bias. (09 Marks)
- b. Design a voltage divider bias circuit using silicon transistor with V<sub>CC</sub> = 18V, I<sub>C</sub> = 2.3mA, V<sub>CE</sub> = 8.2V, R<sub>C</sub> = 3.3kΩ, β = 100 and S(I<sub>CO</sub>) ≤ 5. (06 Marks)
- c. For the transistor switch in shown Fig.Q2(c), V<sub>BE</sub> = 0.7V, (V<sub>CE</sub>)<sub>sat</sub> = 0.3V, I<sub>CEo</sub> = 5μA and h<sub>fe</sub> = 125. i) Calculate (I<sub>C</sub>)<sub>sat</sub> (I<sub>B</sub>)<sub>max</sub>, On and Off resistance (R)<sub>sat</sub> and (R)<sub>cut off</sub> ii) Sketch output voltage wave form. (05 Marks)

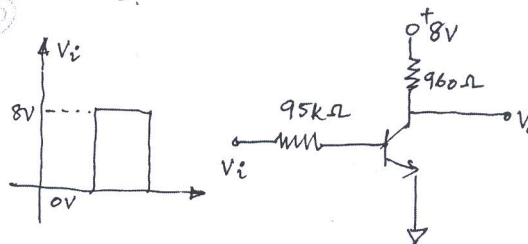


Fig.Q2(c)  
1 of 3

Important Note : 1. On completing your answers, compulsorily draw diagonal cross lines on the remaining blank pages.  
 2. Any revealing of identification, appeal to evaluator and /or equations written eg, 42+8 = 50, will be treated as malpractice.

- 3 a. Derive an expression for  $Z_i$ ,  $Z_o$ ,  $A_v$  and  $A_i$  for common-base configuration using  $r_e$  model. Also discuss some applications of CB configuration. (10 Marks)
- b. For the emitter follower circuit shown in Fig.Q3(b), calculate  $r_e$ ,  $Z_i$ ,  $Z_o$ ,  $A_v$  and  $A_i$ . Take  $\beta = 100$  and  $r_o = \infty$ . (05 Marks)

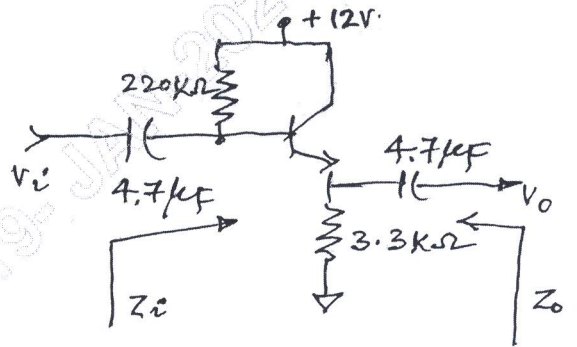


Fig.Q3(b)

- c. For the circuit shown in Fig.Q3(c) below calculate  $r_e$ ,  $Z_i$ ,  $Z_o$ ,  $A_v$  and  $A_i$ . Take  $\beta = 140$  and  $r_o = 30k\Omega$ .

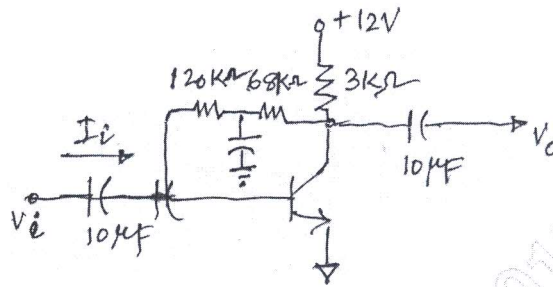


Fig.Q3(c)

(05 Marks)

- 4 a. Prove that miller effect of input capacitance  $C_{Mi} = (1 - A_v)C_f$  and output capacitance  $C_{Mo} = [1 - 1/A_v] C_f$  and also discuss applications of Millers theorem. (10 Marks)
- b. For the circuit shown in Fig.Q4(b) the following, using transistor with  $\beta = 100$  and  $r_o = \infty\Omega$ .
- $r_e$
  - input resistance  $R_i$
  - mid band voltage gain  $A_v = V_o/V_i$  and  $A_{vS} = V_o/V_S$
  - lower cut off frequency due to  $C_S$
  - lower cut off frequency due to  $C_C$  and  $C_E$
  - overall lower cut off frequency.

(10 Marks)

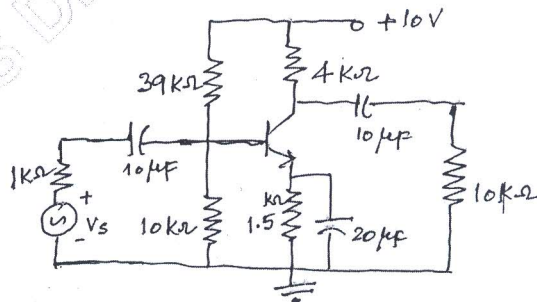


Fig.Q4(b)

PART - B

- 5 a. Derive expressions for  $Z_i$  and  $A_i$  for Darlington emitter follower circuit. (08 Marks)  
 b. For the current series feedback amplifier shown in Fig.Q5(b) calculate the following :  
 i) Densensitivity factor  
 ii) Transfer gain with feedback  
 iii) Voltage gain with and without feedback  
 iv) Input resistance with and without feedback  
 v) Output resistance with and without feedback  
 vi) Output current with and without feedback  
 vii) Output voltage with and without feedback. (12 Marks)

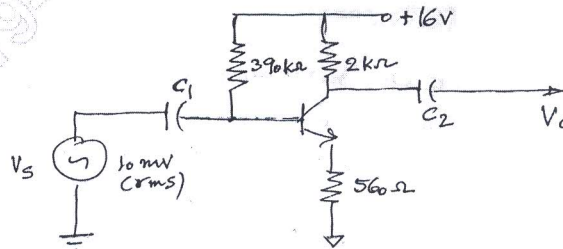


Fig.Q5(b)

- 6 a. Explain the operation of a class-B push pull amplifier and derive an expression for conversion efficiency. (08 Marks)  
 b. Draw the circuit of transformer coupled class A power amplifier, on performing DC and AC analysis. Derive an expression for AC power delivered to load and maximum AC output power. (12 Marks)
- 7 a. Explain the working of Wein bridge oscillator. (06 Marks)  
 b. With a neat circuit diagram, explain the operation of Hartley oscillator. (06 Marks)  
 c. Discuss the merits, demerits and application of crystal oscillators. (04 Marks)  
 d. A crystal has following parameters :  $L = 0.334\text{H}$   $C = 0.065\text{ pf}$   $C_M = 1\text{ pf}$   $R = 5.5\text{ k}\Omega$ .  
 i) Calculate series and parallel frequency.  
 ii) By what percentage does parallel resonant frequency exceeds the series resonant frequency  
 iii) Find the 'Q' of the crystal. (04 Marks)
- 8 a. Compare JFET and MOSFET. (04 Marks)  
 b. Draw the circuit of JFET common gate configuration. Derive an expression for  $Z_i$ ,  $Z_0$  and  $A_v$  using small signal model. Also summarize the characteristic of common gate configuration. (10 Marks)  
 c. For the JFET-common drain configuration shown in Fig.Q8(c) and for given data. Calculate  $Z_i$ ,  $Z_0$  and  $A_v$ . Find  $V_0$  if  $V_i = 20\text{ mV}_{(p-p)}$ .

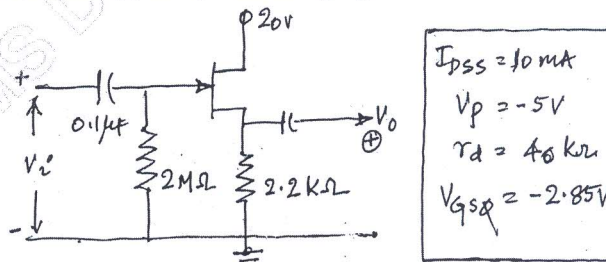


Fig.Q8(c)

(06 Marks)